

MBR1070CT - MBR10100CT

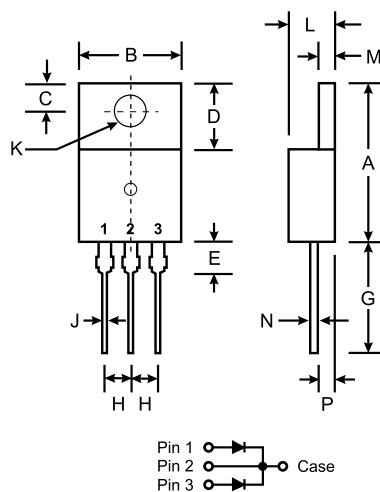
10A HIGH VOLTAGE SCHOTTKY BARRIER RECTIFIER

Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- Plastic Material: UL Flammability Classification Rating 94V-0

Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: As Marked on Body
- Weight: 2.24 grams (approx)
- Mounting Position: Any
- Marking: Type Number



TO-220AB		
Dim	Min	Max
A	14.22	15.88
B	9.65	10.67
C	2.54	3.43
D	5.84	6.86
E	—	6.35
G	12.70	14.73
H	2.29	2.79
J	0.51	1.14
K	3.53Ø	4.09Ø
L	3.56	4.83
M	1.14	1.40
N	0.30	0.64
P	2.03	2.92

All Dimensions in mm

Maximum Ratings and Electrical Characteristics

@ $T_A = 25^\circ\text{C}$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristic	Symbol	MBR 1070CT	MBR 1080CT	MBR 1090CT	MBR 10100CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWMM} V_R	70	80	90	100	V
RMS Reverse Voltage	$V_{R(\text{RMS})}$	49	56	63	70	V
Average Rectified Output Current (Note 1) @ $T_C = 100^\circ\text{C}$	I_O			10		A
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}			120		A
Forward Voltage Drop @ $I_F = 5.0\text{A}$, $T_C = 125^\circ\text{C}$ @ $I_F = 5.0\text{A}$, $T_C = 25^\circ\text{C}$ @ $I_F = 10\text{A}$, $T_C = 125^\circ\text{C}$ @ $I_F = 10\text{A}$, $T_C = 25^\circ\text{C}$	V_{FM}			0.75 0.85 0.85 0.95		V
Peak Reverse Current at Rated DC Blocking Voltage @ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	I_{RM}			0.1 50		mA
Typical Junction Capacitance (Note 2)	C_J			300		pF
Typical Thermal Resistance Junction to Case (Note 1)	$R_{\theta JC}$			3.0		K/W
Voltage Rate of Change	dV/dt			10,000		V/ μ s
Operating and Storage Temperature Range	T_j, T_{STG}			-65 to +150		°C

Notes:

1. Thermal resistance junction to case mounted on heatsink.
2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

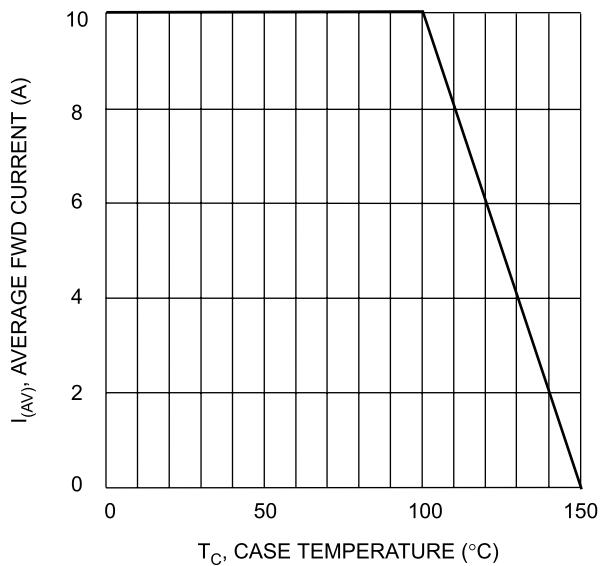


Fig. 1 Forward Current Derating Curve

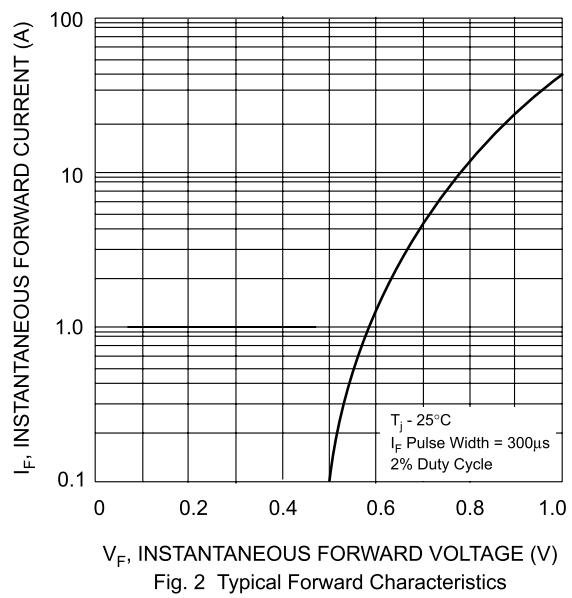


Fig. 2 Typical Forward Characteristics

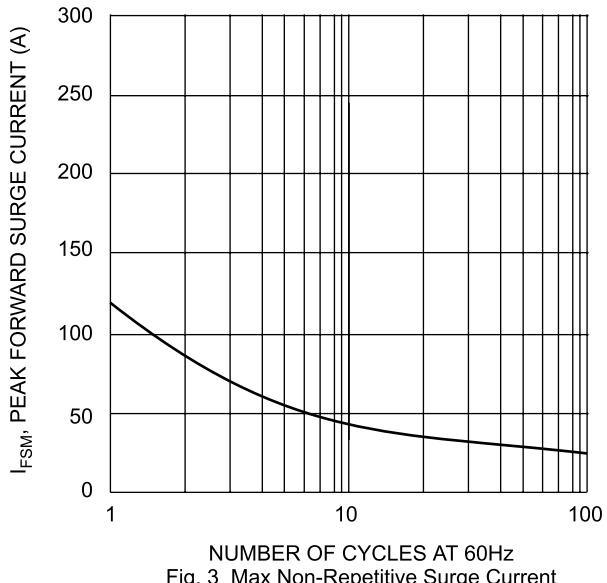


Fig. 3 Max Non-Repetitive Surge Current

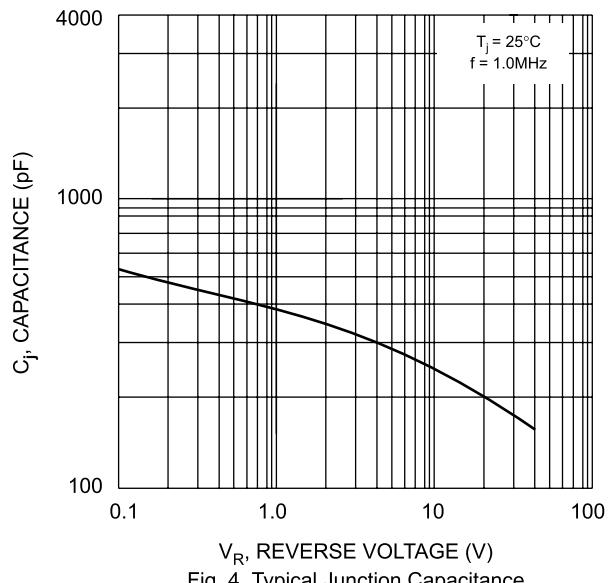


Fig. 4 Typical Junction Capacitance